2SD2101

Silicon NPN Triple Diffused

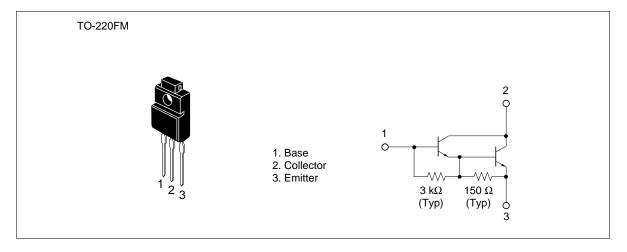
HITACHI

ADE-208-920 (Z) 1st. Edition Sep. 2000

Application

Low frequency power amplifier

Outline





2SD2101

Absolute Maximum Ratings (Ta = 25°C)

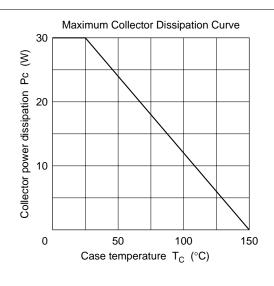
Item	Symbol	Rating	Unit	
Collector to base voltage	V_{CBO}	200	V	
Collector to emitter voltage	V _{CEO}	200	V	
Emitter to base voltage	V _{EBO}	7	V	
Collector current	I _c	10	A	
Collector peak current	I _{C(peak)}	15	A	
Collector power dissipation	P _c	2	W	
	P _c *1	30		
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

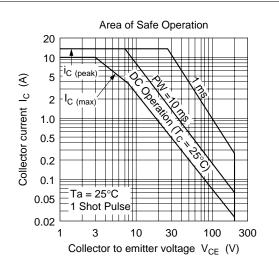
Note: 1. Value at $T_c = 25^{\circ}C$.

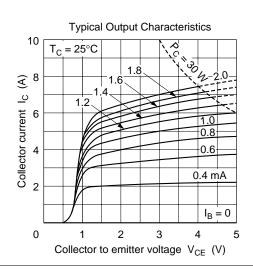
Electrical Characteristics (Ta = 25°C)

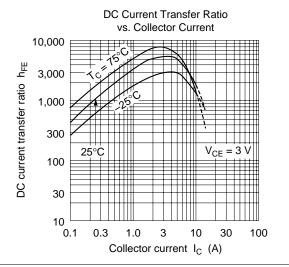
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	200	_	_	V	$I_{\rm C} = 0.1 \text{ mA}, I_{\rm E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	200	_	_	V	I_{C} = 25 mA, R_{BE} = ∞
Collector to emitter sustain voltage	$V_{CEO(SUS)}$	170	_	_	V	I _C = 5 A, L = 5 mH
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	_	_	V	$I_{\rm E} = 50 \text{ mA}, I_{\rm C} = 0$
Collector cutoff current	I _{CBO}	_	_	10	μΑ	V _{CB} = 180 V, I _E = 0
	I _{CEO}	_	_	50		V _{CE} = 180 V, R _{BE} = ∞
DC current transfer ratio	h _{FE}	1500	_	_		$V_{CE} = 3 \text{ V}, I_{C} = 5 \text{ A}^{*1}$
Collector to emitter saturation	V _{CE(sat)1}	_	_	1.5	V	$I_{\rm C} = 5 \text{ A}, I_{\rm B} = 10 \text{ mA}^{*1}$
voltage	V _{CE(sat)2}	_	_	3.0		$I_{\rm C} = 10 \text{ A}, I_{\rm B} = 100 \text{ mA}^{*1}$
Base to emitter saturation	V _{BE(sat)1}	_	_	2.0	V	$I_{\rm C} = 5 \text{ A}, I_{\rm B} = 10 \text{ mA}^{*1}$
voltage	V _{BE(sat)2}	_	_	3.5		$I_{\rm C}$ = 10 A, $I_{\rm B}$ = 100 mA* ¹

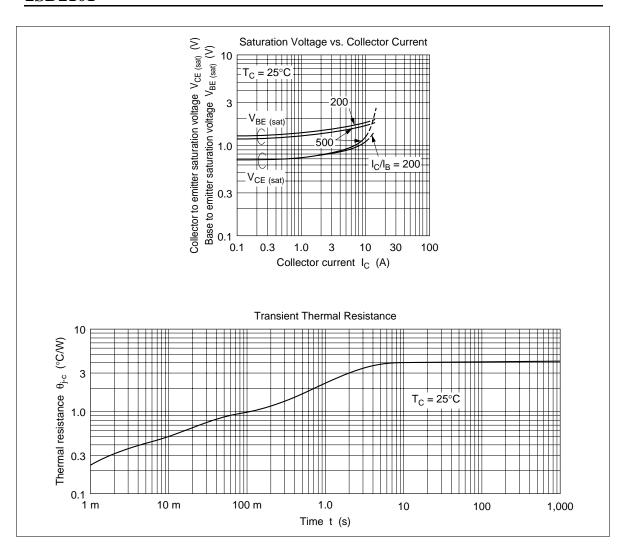
Note: 1. Pulse test.



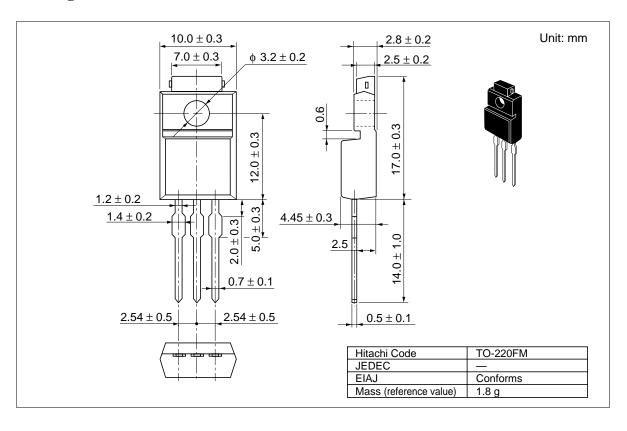








Package Dimensions



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